

IN THE SPECIFICATION:

Please amend the last paragraph of page 11 as follows:

The semiconductor chip 20 is a center-bonding type semiconductor chip having center-bonding pads formed on the upper surface thereof as shown in Fig. 4i. On the semiconductor chip 20 are formed edge-bonding metal patterns 26, which are electrically connected to the center-bonding pads 21 of the semiconductor chip 20 in a wafer level by means of a prescribed process, for example, sputtering. The edge-bonding metal patterns 26 are extended towards the edge regions of the center-bonding type semiconductor chip so that they are also electrically connected to the corresponding circuit patterns 11 of the substrate 10 ~~[[be]]~~ by means of the connection members 30. The semiconductor chip is mounted on the substrate 10 by means of the bonding agent 60.

Please amend the third paragraph of page 19 as follows:

Subsequently, the semiconductor chip 20 having the edge-bonding metal patterns 26 formed thereon, which is ~~sawn by~~ cut into units of the prescribed semiconductor chip size, is attached to the substrate 10 having the circuit patterns 11 formed therein, which are formed in a prescribed shape for electric connection, by means of the bonding agent 60 (S500).

Please amend the paragraph starting from line 7 of page 20 as follows:

Finally, the packaged substrate molded with the sealing material 40 is ~~sawn by~~ cut into units of a prescribed size to obtain a BGA package having a semiconductor chip with the edge-bonding metal patterns 26 formed thereon in a wafer level (S900).

Please amend the last paragraph of page 26 as follows:

After the semiconductor chip 20 having the edge-bonding metal patterns 26 formed thereon is realized on the wafer as described above, the metal-patterned wafer is ~~sawn by~~ cut into units of a prescribed semiconductor chip size by means of a blade (S400).

Please amend the first paragraph of page 27 as follows:

Subsequently, the semiconductor chip 20 having the edge-bonding metal patterns 26 formed thereon, which is ~~sawn by~~ cut into units of the prescribed semiconductor chip size, is attached to the substrate 10 having the circuit patterns 11 formed therein, which are formed in a prescribed shape for electric connection, by means of the bonding agent 60 (S500).

Please amend the last paragraph of page 28 as follows:

Finally, the packaged substrate molded with the sealing material 40 is ~~sawn by~~ cut into units of a prescribed size to obtain a multi-layered BGA package having semiconductor chips with the edge-bonding metal patterns 26 formed thereon in a wafer level (S1200).